

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1           Claim 1 (currently amended): A method for manufacturing a semiconductor device,  
2           comprising the steps of:

3           (a) forming a laminated substrate by laminating a device formation layer consisting of single  
4           crystalline semiconductor on a supporting substrate consisting of single crystalline semiconductor  
5           via an insulating layer wherein a direction of a crystallographic axis of the device formation layer  
6           is shifted from a corresponding crystallographic axis of the supporting substrate;

7           (b) forming semiconductor devices on the device formation layer within a plurality of areas  
8           divided by scribe lines, the scribe lines being defined on the device formation layer and not on the  
9           supporting substrate, the scribe lines extending to a direction being parallel to a direction of a  
10          crystallographic axis of the supporting substrate where the supporting substrate is easy to be cleaved;  
11          and

12          (c) splitting the laminated substrate into a plurality of chips by cleaving the supporting  
13          substrate along the scribe lines;

14          wherein the step (b) further comprises the step of forming a wiring layer comprising wiring

15 wherein at least 70% of a full length of all the wiring in the wiring layer extends to a direction being  
16 substantially parallel to a direction of a crystallographic axis of the supporting substrate where the  
17 supporting substrate is easy to be cleaved.

1 Claim 2 (original): A method for manufacturing a semiconductor device according to claim  
2 1, further comprising, between the step (b) and the step (c), the step of forming grooves reaching at  
3 least a bottom of the device formation layer from a surface of the device formation layer along the  
4 scribe lines.

1 Claim 3 (original): A method for manufacturing a semiconductor device according to claim  
2 1, wherein  
3 the supporting substrate and the device formation layer consist of single crystalline silicon,  
4 orientation of crystal plane of laminating surfaces of both supporting substrate and device  
5 formation layer is [100] plane, and  
6 a <110> direction of the device formation layer is shifted from a <110> direction of the  
7 supporting substrate just at an angle of 42 to 48 degree.

1 Claim 4 (original): A method for manufacturing a semiconductor device according to claim  
2 3, wherein the scribe lines are parallel to the <110> direction of the supporting substrate.

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1           Claim 5 (original): A method for manufacturing a semiconductor device according to claim  
2           3, wherein the step (b) further comprises the step of forming an active device on the device formation  
3           layer, a moving direction of carrier of active device being the <100> direction of the device  
4           formation layer.

Claim 6 (canceled).

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